First Hit

End of Result Set

Generate Collection Print

L4: Entry 4 of 4

File: DWPI

Mar 11, 2004

DERWENT-ACC-NO: 2002-257704

DERWENT-WEEK: 200419

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TITLE: <u>Cleaning</u> of apparatus for semiconductor production involves repeating appropriate <u>cleaning</u> process on parts to be cleaned until maximum acceptable impurity level is reached

Basic Abstract Text (1):

NOVELTY - A definition for a clean part including multiple maximum acceptable impurity levels is determined and a part to be cleaned is tested to determine its incoming impurity levels. An appropriate cleaning process is determined and applied to the part to be cleaned. After cleaning process, the reduced impurity level is compared with the maximum level, for repeating the cleaning process application.

Basic Abstract Text (2):

DETAILED DESCRIPTION - The <u>impurity levels</u> in the parts to be cleaned, is determined using surface particle test, liquid particle test, acid extraction ICP-MS techniques. INDEPENDENT CLAIMS are also included for the following:

Basic Abstract Text (3):

(a) dilute aqueous <u>cleaning</u> solution for parts;

Basic Abstract Text (5):

(c) process for <u>determining</u> contamination of an operable part;

Basic Abstract Text (6):

(d) process for <u>cleaning</u> ceramic parts;

Basic Abstract Text (7):

(e) process for <u>cleaning</u> textured quartz parts;

Basic Abstract Text (8):

(f) process for cleaning metallic impurities from textured ceramic surfaces;

Basic Abstract Text (9):

(g) process for <u>cleaning</u> metallic impurities;

Basic Abstract Text (10):

(h) process for <u>determining</u> cleanliness of <u>semiconductor fabrication equipment</u> parts; and

Basic Abstract Text (11):

(i) process for removing particles on a textured surface or <u>semiconductor</u> fabrication equipment part.

Basic Abstract Text (12):

USE - Used for <u>cleaning</u> semiconductor manufacturing apparatus parts such as CVD and etch chamber parts.

Basic Abstract Text (13):

ADVANTAGE - Reduces <u>cleaning</u> defects by use of repeated testing of <u>impurity levels</u> after each pass through the <u>cleaning</u> process. Achieves particular <u>impurity level</u> goals with increased accuracy and the part can be certified to meet actual specification based on either needs for cleanliness in the semiconductor process.

Basic Abstract Text (14):

DESCRIPTION OF DRAWING(S) - The figure shows a flowchart illustrating general process guideline for cleaning semiconductor fabrication equipment parts.

Hit List

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 6 of 6 returned.

1. Document ID: US 20040045574 A1

Using default format because multiple data bases are involved.

L2: Entry 1 of 6

File: PGPB

Mar 11, 2004

PGPUB-DOCUMENT-NUMBER: 20040045574

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040045574 A1

TITLE: System and method for cleaning semiconductor fabrication equipment parts

PUBLICATION-DATE: March 11, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Tan, Samantha

Union City

CA

US

US-CL-CURRENT: $\underline{134/1}$; $\underline{134/26}$, $\underline{252/79.1}$, $\underline{510/175}$

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims RVAC Draw Do

2. Document ID: US 20020066466 A1

L2: Entry 2 of 6

File: PGPB

Jun 6, 2002

PGPUB-DOCUMENT-NUMBER: 20020066466

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20020066466 A1

TITLE: Cleaning of semiconductor process equipment chamber parts using organic

solvents

PUBLICATION-DATE: June 6, 2002

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Tan, Samantha

Union City

CA

US

US-CL-CURRENT: 134/3; 134/105, 134/18, 134/28, 134/30, 134/35, 134/37, 134/6

ABSTRACT:

h eb b g ee ef eh ef b

A system and method are provided for using an organic solvent to clean chamber parts used in semiconductor manufacturing. The chamber parts are exposed to the solvent using a dipping system or a vapor contact system in order to soften or dissolve the organic polymers. The solvent may be heated up to a temperature of 100.degree. C. The organic cleaning solvent may be a pyrrole-based, amine-based, fluoro/ether-based or ether-based solvent. Additionally, a system and method are provided for establishing criteria to verify that the chamber parts are clean with respect to organic, metallic and particulate impurities and establishing criteria to verify that the physical surface morphology remains intact.

Full	Title	Citation	Frent	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWWC Draw De

3. Document ID: US 6695984 B1

L2: Entry 3 of 6

File: USPT

Feb 24, 2004

US-PAT-NO: 6695984

DOCUMENT-IDENTIFIER: US 6695984 B1

TITLE: Silicon carbide sinter and process for producing the same

DATE-ISSUED: February 24, 2004

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Odaka; Fumio Niiza JP
Takahashi; Yoshitomo Fujisawa JP

US-CL-CURRENT: <u>252/504</u>; <u>252/500</u>, <u>252/516</u>, <u>252/521.3</u>, <u>264/625</u>, <u>423/345</u>, <u>423/439</u>, <u>501/88</u>, <u>501/92</u>

ABSTRACT:

The present invention provides: a fabrication method of a silicon carbide sintered body, including a step of fabricating a mixed powder slurry by dissolving or dispersing silicon carbide powder, at least one organic material composed of a nitrogen source, and at least one organic material composed of a carbon source or carbon powder in a solvent, a step of fabricating a green body by pouring the mixed powder slurry into a mold and drying and a step of filling pores in the green body by immersing the green body in high purity metallic silicon that has been heated to 1450 to 1700.degree. C. in a vacuum atmosphere or inert gas atmosphere and melted, and generating silicon carbide by reacting silicon sucked up into the pores in the green body by capillary action with free carbon in the green body; and a silicon carbide sintered body obtained by a reaction sintering method, having a density of 2.90 g/cm.sup.3 or more and a volume resistivity of 10.sup.0 .OMEGA..multidot.cm or less, and containing nitrogen at 150 ppm or more.

7 Claims, 3 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 2

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims KMC Draw De

ef

b

4. Document ID: US 6607605 B2

L2: Entry 4 of 6

File: USPT

Aug 19, 2003

US-PAT-NO: 6607605

DOCUMENT-IDENTIFIER: US 6607605 B2

TITLE: Cleaning of semiconductor process equipment chamber parts using organic

solvents

DATE-ISSUED: August 19, 2003

INVENTOR-INFORMATION:

NAME

CITY

STATE

ZIP CODE

COUNTRY

Tan; Samantha

Union City

CA

US-CL-CURRENT: $\underline{134/3}$; $\underline{134/18}$, $\underline{134/19}$, $\underline{134/2}$, $\underline{134/22.1}$, $\underline{134/22.19}$, $\underline{134/26}$, $\underline{134/30}$, $\underline{134/31}$, $\underline{134/34}$, $\underline{438/905}$

ABSTRACT:

A system and method are provided for using an organic solvent to clean chamber parts used in semiconductor manufacturing. The chamber parts are exposed to the solvent using a dipping system or a vapor contact system in order to soften or dissolve the organic polymers. The solvent may be heated up to a temperature of 100.degree. C. The organic cleaning solvent may be a pyrrole-based, amine-based, fluoro/ether-based or ether-based solvent. Additionally, a system and method are provided for establishing criteria to verify that the chamber parts are clean with respect to organic, metallic and particulate impurities and establishing criteria to verify that the physical surface morphology remains intact.

15 Claims, 6 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 6

Fuil	Title	Citation	Front	Review	Classification	Date	Reference	Claims KWC Draw De

5. Document ID: US 6607605 B2, WO 200219390 A2, US 20020066466 A1, AU 200188629 A

L2: Entry 5 of 6

File: DWPI

Aug 19, 2003

DERWENT-ACC-NO: 2002-393774

DERWENT-WEEK: 200356

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TITLE: Cleaning of semiconductor fabrication equipment parts involves immersing the

part into organic solvent to soften or dissolve organic polymers

INVENTOR: TAN, S; CHEN, N

PRIORITY-DATA: 2000US-229615P (August 31, 2000), 2001US-0945259 (August 31, 2001)

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
<u>US 6607605 B2</u>	August 19, 2003		000	C23G001/02
WO 200219390 A2	March 7, 2002	E	023	H01L000/00
US 20020066466 A1	June 6, 2002		000	B08B003/04
<u>AU 200188629 A</u>	March 13, 2002		000	H01L000/00

INT-CL (IPC): $\underline{\text{B08}}$ $\underline{\text{B}}$ $\underline{3/04}$; $\underline{\text{C23}}$ $\underline{\text{G}}$ $\underline{1/02}$; $\underline{\text{H01}}$ $\underline{\text{L}}$ $\underline{0/00}$

Full Title Citation Front Review Classification Date Reference Claims KMC: Draw De

6. Document ID: US 20040045574 A1, WO 200215255 A1, AU 200186453 A, TW 495863 A, EP 1320879 A1

L2: Entry 6 of 6

File: DWPI

Mar 11, 2004

DERWENT-ACC-NO: 2002-257704

DERWENT-WEEK: 200419

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TITLE: <u>Cleaning</u> of apparatus for semiconductor production involves repeating appropriate <u>cleaning</u> process on parts to be cleaned until maximum acceptable impurity level is reached

INVENTOR: TAN, S

PRIORITY-DATA: 2000US-224582P (August 11, 2000), 2001US-0927263 (August 10, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
US 20040045574 A1	March 11, 2004		000	B08B003/12
WO 200215255 A1	February 21, 2002	E	043	H01L021/461
AU 200186453 A	February 25, 2002		000	H01L021/461
TW 495863 A	July 21, 2002		000	H01L021/30
EP 1320879 A1	June 25, 2003	E	000	H01L021/461

INT-CL (IPC): $\underline{B08} \ \underline{B} \ \underline{3/12}$; $\underline{H01} \ \underline{L} \ \underline{21/30}$; $\underline{H01} \ \underline{L} \ \underline{21/461}$

Full Title Citation Front Review Classification Date Reference	Claims Kootc
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CLEANING).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD.

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Search Results - Record(s) 1 through 2 of 2 returned.

1. Document ID: US 20040045574 A1

Using default format because multiple data bases are involved.

L6: Entry 1 of 2

File: PGPB

Mar 11, 2004

PGPUB-DOCUMENT-NUMBER: 20040045574

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040045574 A1

TITLE: System and method for <u>cleaning semiconductor fabrication equipment parts</u>

PUBLICATION-DATE: March 11, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Tan, Samantha

Union City

CA

US

US-CL-CURRENT: <u>134/1</u>; <u>134/26</u>, <u>252/79.1</u>, <u>510/175</u>

Full Title Citation Front	Review Classification	Date Reference	Sequences Attachments	Claims KWC Draw De
				3

2. Document ID: US 20040045574 A1, WO 200215255 A1, AU 200186453 A, TW 495863 A, EP 1320879 A1

L6: Entry 2 of 2

File: DWPI

Mar 11, 2004

DERWENT-ACC-NO: 2002-257704

DERWENT-WEEK: 200419

COPYRIGHT 2004 DERWENT INFORMATION LTD

TITLE: <u>Cleaning</u> of apparatus for semiconductor production involves repeating appropriate <u>cleaning</u> process on parts to be cleaned until maximum acceptable

impurity level is reached

INVENTOR: TAN, S

PRIORITY-DATA: 2000US-224582P (August 11, 2000), 2001US-0927263 (August 10, 2001)

PATENT-FAMILY:

PUB-NO PUB-DATE LANGUAGE PAGES MAIN-IPC US 20040045574 A1 March 11, 2004 000 B08B003/12 February 21, 2002 WO 200215255 A1 043 H01L021/461 AU 200186453 A February 25, 2002 000 H01L021/461

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TW 495863 A EP 1320879 A1 July 21, 2002

June 25, 2003

E

000 000

H01L021/30 H01L021/461

INT-CL (IPC): $\underline{\text{B08}}$ $\underline{\text{B}}$ $\underline{\text{3}}/\underline{\text{12}}$; $\underline{\text{H01}}$ $\underline{\text{L}}$ $\underline{\text{21}}/\underline{\text{30}}$; $\underline{\text{H01}}$ $\underline{\text{L}}$ $\underline{\text{21}}/\underline{\text{461}}$

Full T	itie Citation Front Review Classification Date Reference	Claims KMC	D
ear	Generate Collection Print Fwd Refs Bkwd Refs	Generate OA	AC:
[Term	Documents	
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	REDUCEDS	22	
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- 11	(L5 AND REDUCED).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD.	2	

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Hit List

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 20040045574 A1

Using default format because multiple data bases are involved.

L4: Entry 1 of 4

File: PGPB

Mar 11, 2004

PGPUB-DOCUMENT-NUMBER: 20040045574

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040045574 A1

TITLE: System and method for cleaning semiconductor fabrication equipment parts

PUBLICATION-DATE: March 11, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Tan, Samantha

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US

US-CL-CURRENT: <u>134/1</u>; <u>134/26</u>, <u>252/79.1</u>, <u>510/175</u>

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KNNC			- Date il Meterence	ប់ក	eview Classification	Front F	- Citation I-	- Title
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2. Document ID: US 20020066466 A1

L4: Entry 2 of 4

File: PGPB

Jun 6, 2002

PGPUB-DOCUMENT-NUMBER: 20020066466

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20020066466 A1

TITLE: Cleaning of semiconductor process equipment chamber parts using organic

solvents

PUBLICATION-DATE: June 6, 2002

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Tan, Samantha

Union City

CA

US

US-CL-CURRENT: $\underline{134}/\underline{3}$; $\underline{134}/\underline{105}$, $\underline{134}/\underline{18}$, $\underline{134}/\underline{28}$, $\underline{134}/\underline{30}$, $\underline{134}/\underline{35}$, $\underline{134}/\underline{37}$, $\underline{134}/\underline{6}$

ABSTRACT:

h eb b g ee ef eh ef b e

A system and method are provided for using an organic solvent to clean chamber parts used in semiconductor manufacturing. The chamber parts are exposed to the solvent using a dipping system or a vapor contact system in order to soften or dissolve the organic polymers. The solvent may be heated up to a temperature of 100.degree. C. The organic cleaning solvent may be a pyrrole-based, amine-based, fluoro/ether-based or ether-based solvent. Additionally, a system and method are provided for establishing criteria to verify that the chamber parts are clean with respect to organic, metallic and particulate impurities and establishing criteria to verify that the physical surface morphology remains intact.

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KWIC Draw D.

3. Document ID: US 6607605 B2

L4: Entry 3 of 4

File: USPT

PG005 20066466 Aug 19, 2003

US-PAT-NO: 6607605

DOCUMENT-IDENTIFIER: US 6607605 B2

TITLE: Cleaning of semiconductor process equipment chamber parts using organic solvents

DATE-ISSUED: August 19, 2003

INVENTOR-INFORMATION:

NAME

CITY

STATE

ZIP CODE

COUNTRY

Tan; Samantha

Union City

CA

US-CL-CURRENT: $\underline{134/3}$; $\underline{134/18}$, $\underline{134/19}$, $\underline{134/2}$, $\underline{134/22.1}$, $\underline{134/22.19}$, $\underline{134/26}$, $\underline{134/30}$, 134/31, 134/34, 438/905

ABSTRACT:

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15 Claims, 6 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 6

Title Citation Front Review Classification Date Reference Claims KWWC Drawt De

4. Document ID: US 20040045574 A1, WO 200215255 A1, AU 200186453 A, TW 495863 A, EP 1320879 A1

h e b b g ee e f e h ef L4: Entry 4 of 4

File: DWPI

Mar 11, 2004

DERWENT-ACC-NO: 2002-257704

DERWENT-WEEK: 200419

COPYRIGHT 2004 DERWENT INFORMATION LTD

TITLE: Cleaning of apparatus for semiconductor production involves repeating appropriate cleaning process on parts to be cleaned until maximum acceptable

impurity level is reached

INVENTOR: TAN, S

PRIORITY-DATA: 2000US-224582P (August 11, 2000), 2001US-0927263 (August 10, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
US 20040045574 A1	March 11, 2004		000	B08B003/12
WO 200215255 A1	February 21, 2002	E	043	H01L021/461
AU 200186453 A	February 25, 2002		000	H01L021/461
TW 495863 A	July 21, 2002		000	H01L021/30
EP 1320879 A1	June 25, 2003	E	000	H01L021/461

INT-CL (IPC): $\underline{B08} \ \underline{B} \ \underline{3/12}; \ \underline{H01} \ \underline{L} \ \underline{21/30}; \ \underline{H01} \ \underline{L} \ \underline{21/461}$

Full Title Citation Front Review Classification Date Reference	Claims Kowic
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Term	Documents
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(L3 AND DETERMINING).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD	4

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